

Silicon NPN Power Transistors

BUL38D

DESCRIPTION

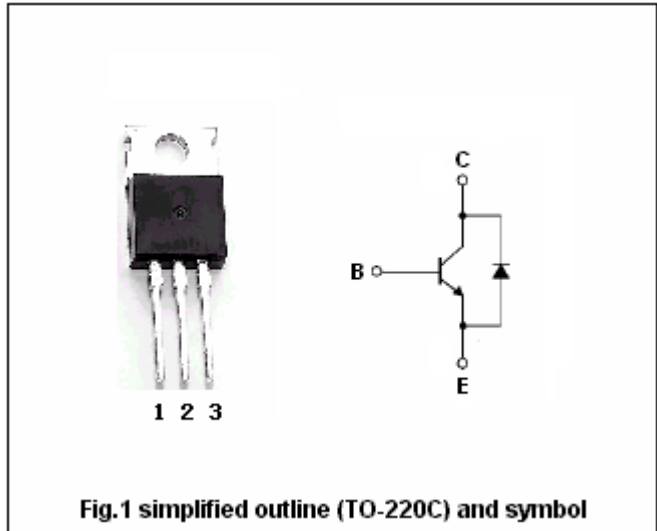
- With TO-220C package
- High voltage ,high speed
- Integrated antiparallel collector-emitter diode

APPLICATIONS

- Designed for use in lighting applications and low cost switch-mode power supplies.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	800	V
V _{CEO}	Collector-emitter voltage	Open base	450	V
V _{EBO}	Emitter-base voltage	Open collector	9	V
I _C	Collector current		5	A
I _{CM}	Collector current-Peak (t _p <5 ms)		10	A
I _B	Base current		2	A
I _{BM}	Base current-Peak (t _p <5 ms)		4	A
P _T	Total power dissipation	T _C =25°C	80	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance from junction to case	1.56	°C/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =100mA; L=25mH	450			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA; I _C =0	9			
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =1A; I _B =0.2A			0.5	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =2A; I _B =0.4A			0.7	V
V _{CEsat-3}	Collector-emitter saturation voltage	I _C =3A; I _B =0.75A			1.1	V
V _{BEsat-1}	Base-emitter saturation voltage	I _C =1A; I _B =0.2A			1.1	V
V _{BEsat-2}	Base-emitter saturation voltage	I _C =2A; I _B =0.4A			1.2	V
I _{CES}	Collector cut-off current	V _{CE} =800V; V _{BE} =0 T _C =125°C			100 500	μ A
I _{CEO}	Collector cut-off current	V _{CE} =450V; I _B =0			250	μ A
h _{FE-1}	DC current gain	I _C =10mA; V _{CE} =5V	10			
h _{FE-2}	DC current gain	I _C =0.5A; V _{CE} =5V			60	
h _{FE-3}	DC current gain	I _C =2A; V _{CE} =5V	13		32	
V _F	Diode forward voltage	I _C =2A			1.5	V

Switching times resistive load

t _s	Storage time	V _{CC} =150V, I _C =2.5A I _{B1} =-I _{B2} =0.5A; t _p =30 μ s	1.0		2.2	μ s
t _f	Fall time				0.8	μ s

◆ h_{FE-1} classifications

A	B
13-23	22-32

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PACKAGE OUTLINE

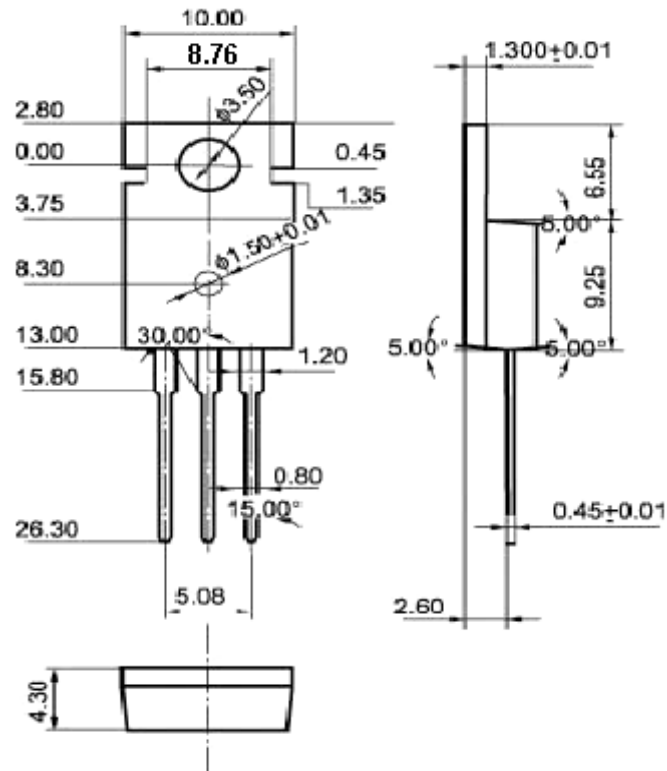


Fig.2 Outline dimensions (unindicated tolerance: 0.1mm)